

Phase out

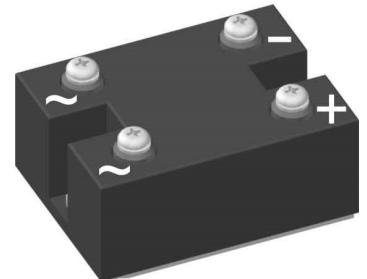
Standard Rectifier Module

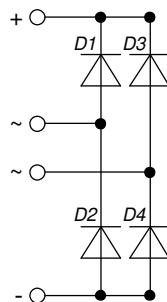
PHASE OUT

1~ Rectifier Bridge

1~ Rectifier	
V_{RRM}	= 800 V
I_{DAV}	= 100 A
I_{FSM}	= 1500 A

Part number

VBO105-08NO7




Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

- Diode for main rectification
- For one phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Package: PWS-C

- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Easy to mount with two screws
- Base plate: Copper internally DCB isolated
- Advanced power cycling

Recommended replacement: VBO130-08NO7

Disclaimer Notice

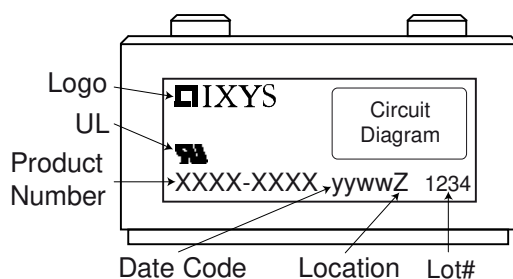
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Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				900	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				800	V
I_R	reverse current	$V_R = 800\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			100	μA
		$V_R = 800\text{ V}$	$T_{VJ} = 150^{\circ}\text{C}$			2	mA
V_F	forward voltage drop	$I_F = 40\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			1.09	V
		$I_F = 80\text{ A}$				1.24	V
		$I_F = 40\text{ A}$	$T_{VJ} = 125^{\circ}\text{C}$			1.00	V
		$I_F = 80\text{ A}$				1.19	V
I_{DAV}	bridge output current	$T_C = 100^{\circ}\text{C}$ rectangular	$T_{VJ} = 150^{\circ}\text{C}$ $d = 0.5$			100	A
V_{F0}	threshold voltage	} for power loss calculation only		$T_{VJ} = 150^{\circ}\text{C}$		0.78	V
r_F	slope resistance					4.8	m Ω
R_{thJC}	thermal resistance junction to case					0.8	K/W
R_{thCH}	thermal resistance case to heatsink				0.3		K/W
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$				155	W
I_{FSM}	max. forward surge current	$t = 10\text{ ms; (50 Hz), sine}$	$T_{VJ} = 45^{\circ}\text{C}$			1.50	kA
		$t = 8,3\text{ ms; (60 Hz), sine}$	$V_R = 0\text{ V}$			1.62	kA
		$t = 10\text{ ms; (50 Hz), sine}$	$T_{VJ} = 150^{\circ}\text{C}$			1.28	kA
		$t = 8,3\text{ ms; (60 Hz), sine}$	$V_R = 0\text{ V}$			1.38	kA
I^2t	value for fusing	$t = 10\text{ ms; (50 Hz), sine}$	$T_{VJ} = 45^{\circ}\text{C}$			11.3	kA ² s
		$t = 8,3\text{ ms; (60 Hz), sine}$	$V_R = 0\text{ V}$			10.9	kA ² s
		$t = 10\text{ ms; (50 Hz), sine}$	$T_{VJ} = 150^{\circ}\text{C}$			8.13	kA ² s
		$t = 8,3\text{ ms; (60 Hz), sine}$	$V_R = 0\text{ V}$			7.87	kA ² s
C_J	junction capacitance	$V_R = 400\text{ V; } f = 1\text{ MHz}$			58		pF

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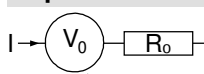
Package PWS-C				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal				150	A
T _{VJ}	virtual junction temperature			-40		150	°C
T _{op}	operation temperature			-40		125	°C
T _{stg}	storage temperature			-40		125	°C
Weight					237		g
M _D	mounting torque			4.25		5.75	Nm
M _T	terminal torque			4.25		5.75	Nm
d _{Spp/App}	creepage distance on surface striking distance through air	terminal to terminal		26.0			mm
d _{Spb/Apb}		terminal to backside		14.0			mm
V _{ISOL}	isolation voltage	t = 1 second	50/60 Hz, RMS; I _{ISOL} ≤ 1 mA	3000			V
		t = 1 minute		2500			V



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VBO105-08NO7	VBO105-08NO7	Box	10	475769

Equivalent Circuits for Simulation

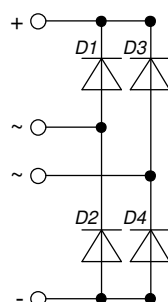
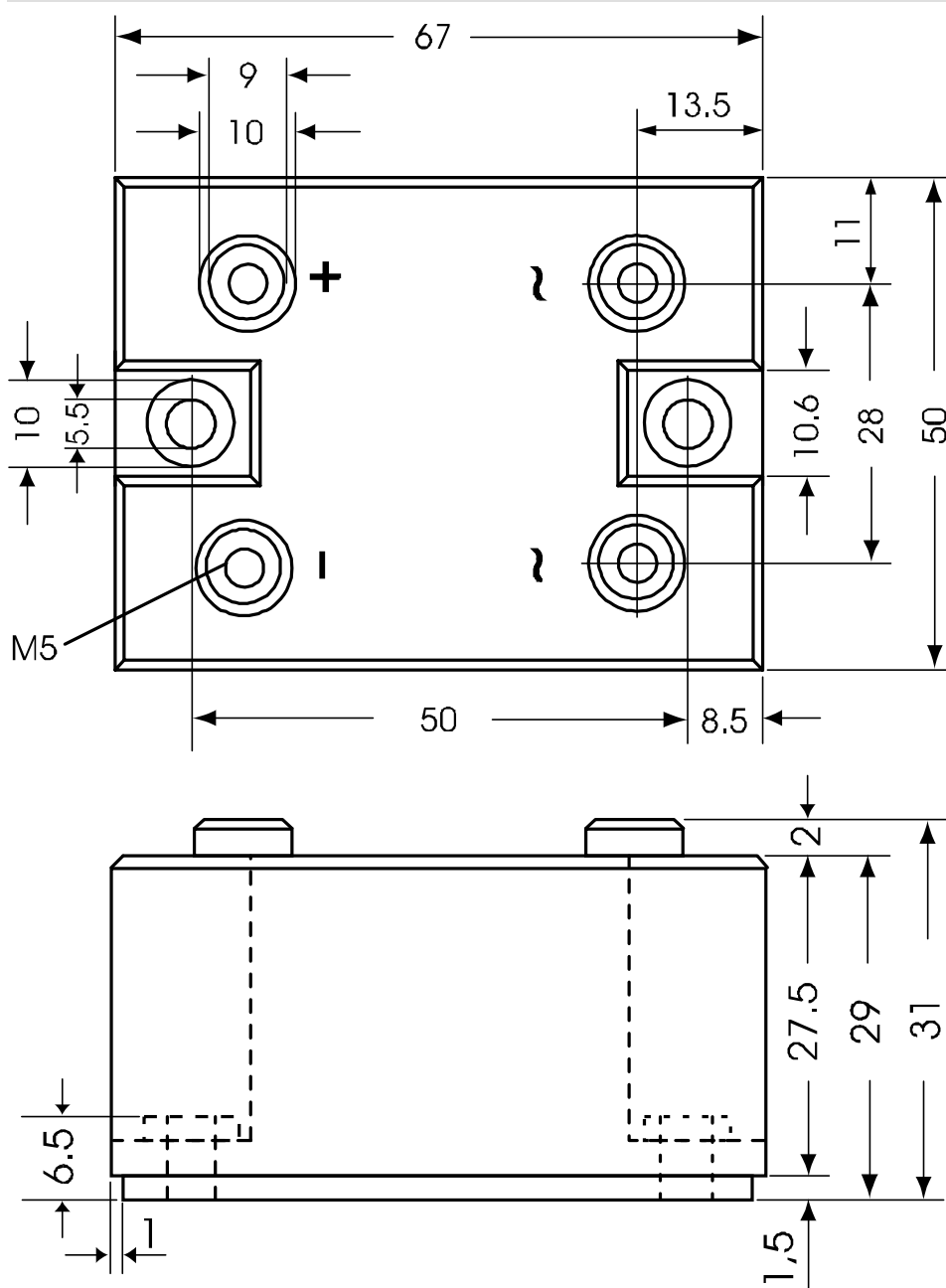
* on die level

 $T_{VJ} = 150^{\circ}\text{C}$


Rectifier

$V_{0\max}$	threshold voltage	0.78	V
$R_{0\max}$	slope resistance *	3.6	mΩ

Outlines PWS-C



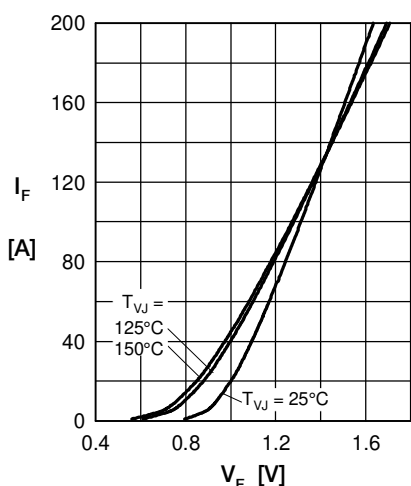
Rectifier


Fig. 1 Forward current versus voltage drop per diode

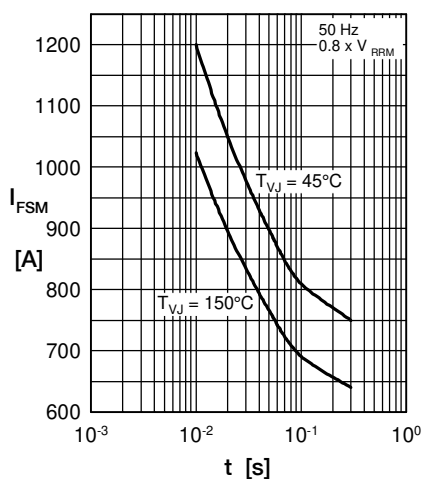


Fig. 2 Surge overload current vs. time per diode

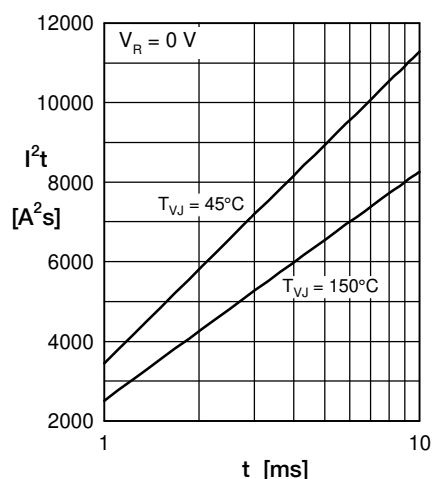
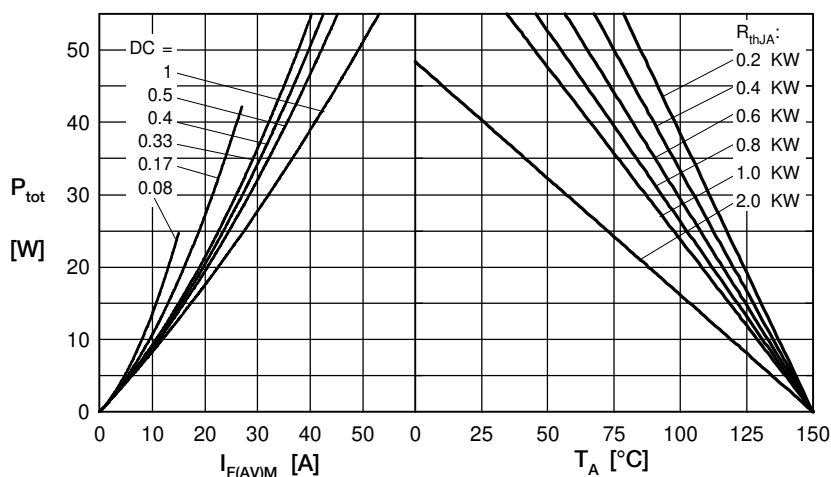

 Fig. 3 I^2t versus time per diode


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

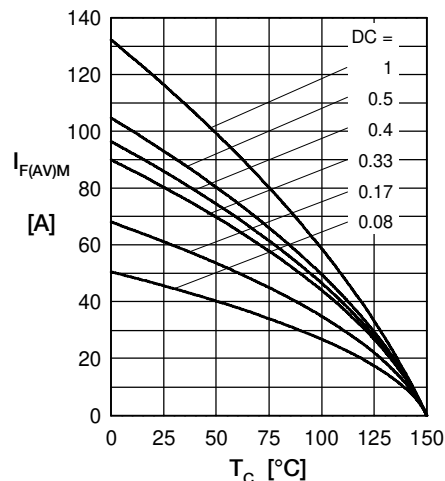


Fig. 5 Max. forward current vs. case temperature per diode

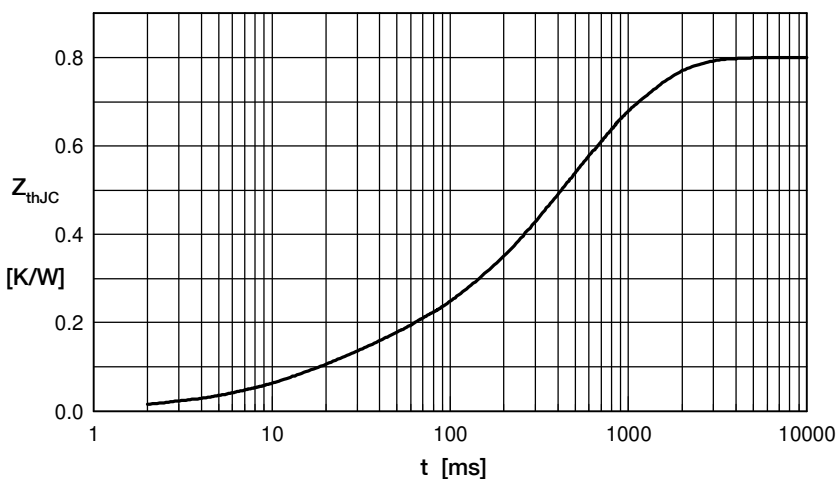


Fig. 6 Transient thermal impedance junction to case vs. time per diode

 Constants for Z_{thJC} calculation:

i	R_{th} (K/W)	t_i (s)
1	0.100	0.020
2	0.014	0.010
3	0.192	0.225
4	0.281	0.800
5	0.213	0.580